Title: TRENCHES TO REDUCE LATERAL SILICIDE GROWTH IN INTEGRATED CIRCUIT TECHNOLOGY
Inventors: Darin A. Chan, et al.
Docket No.: H1844
Contact: Mikio Ishimaru (408) 738-0592

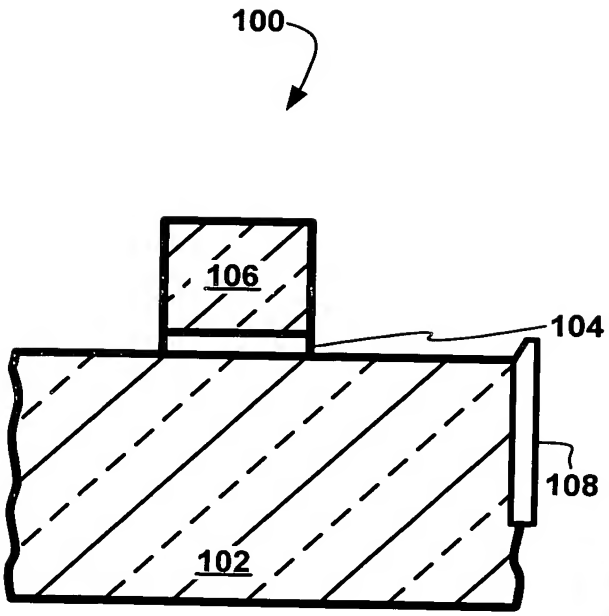

FIG. 1

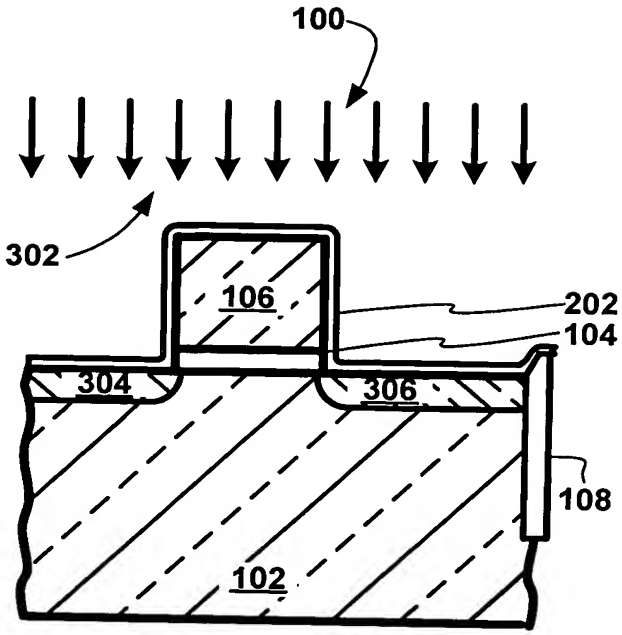

FIG.3

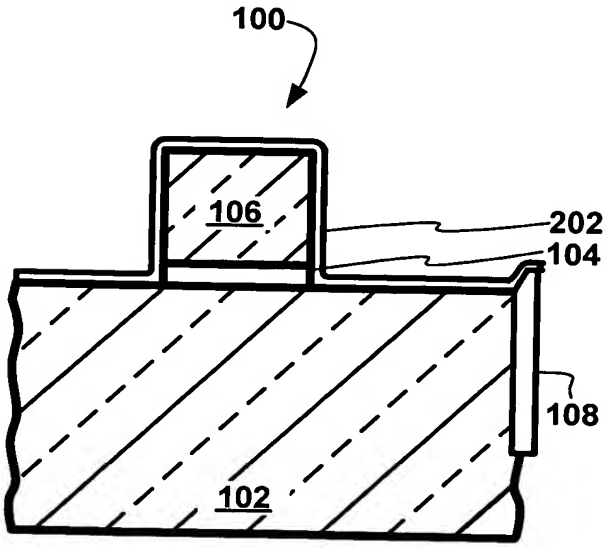

FIG. 2

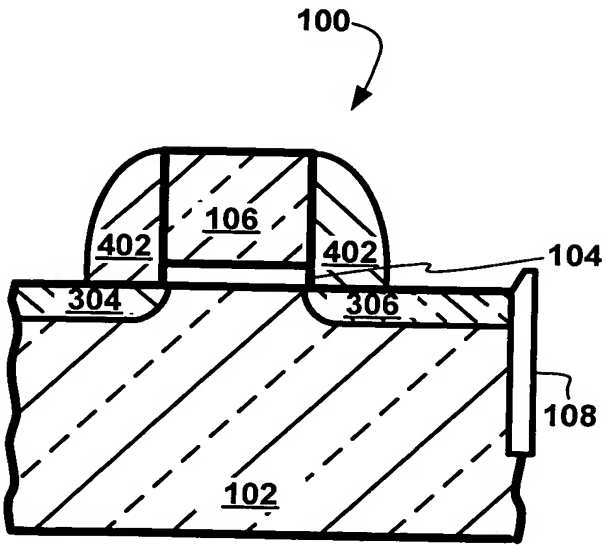

FIG. 4

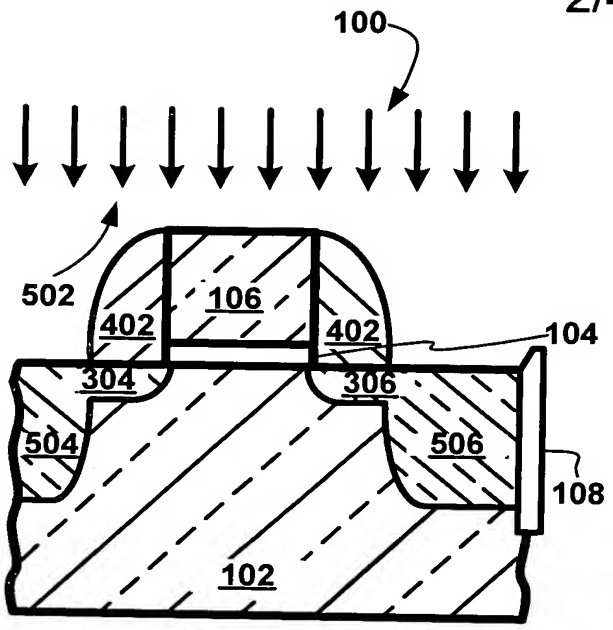

FIG. 5

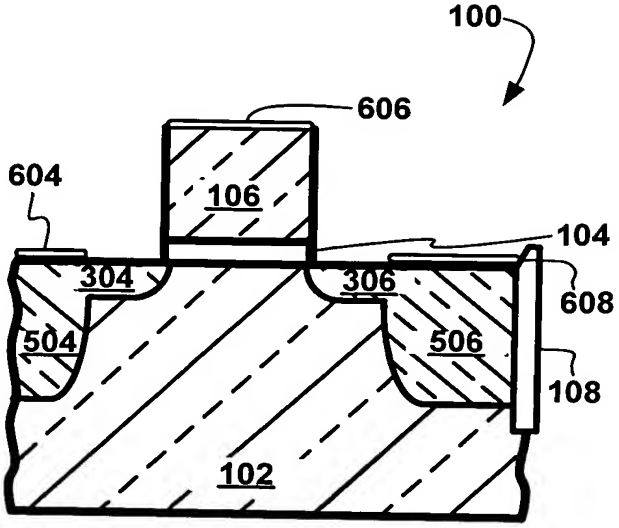

FIG. 7

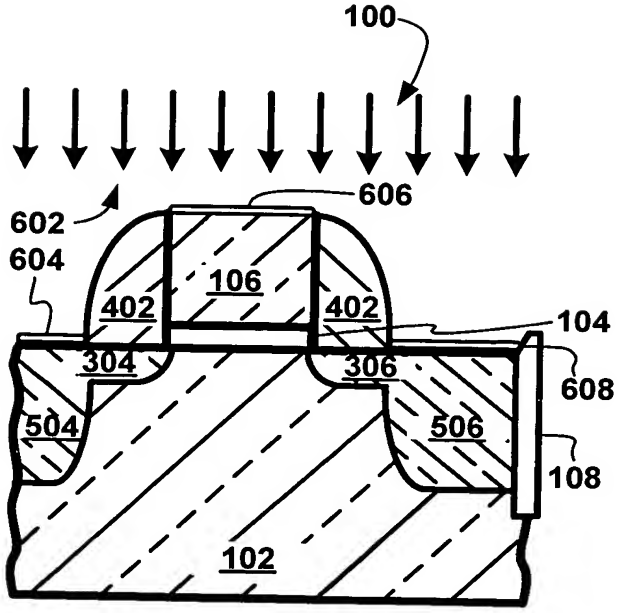

FIG. 6

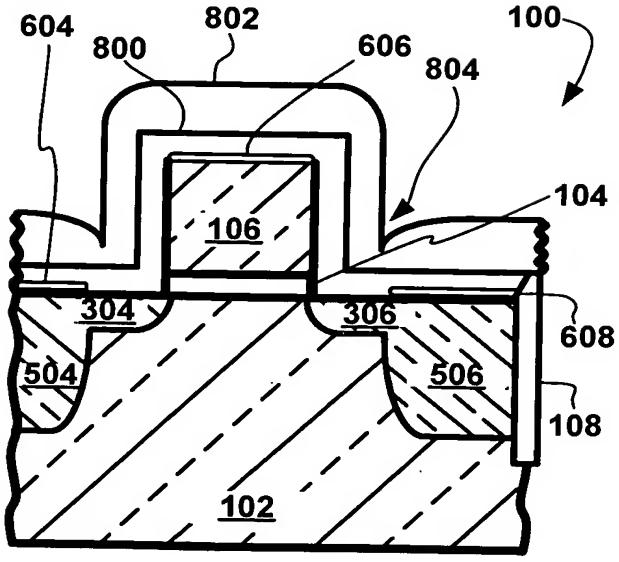

FIG. 8

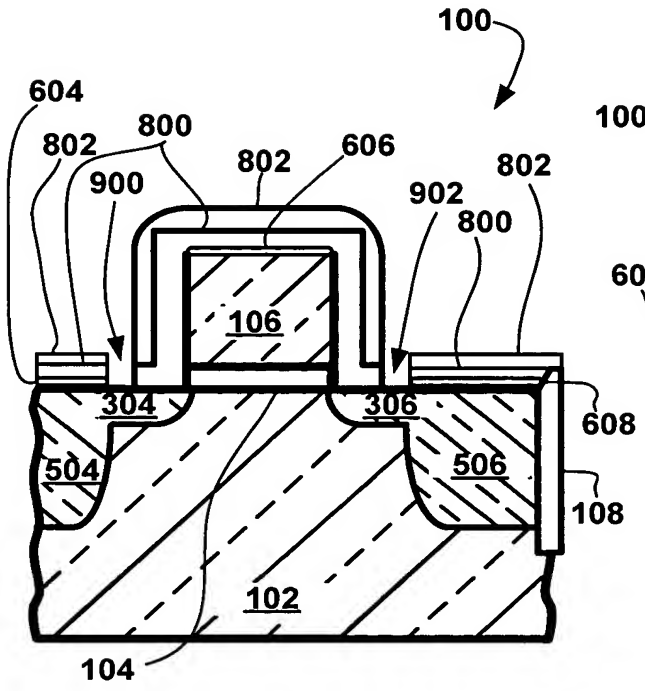

FIG. 9

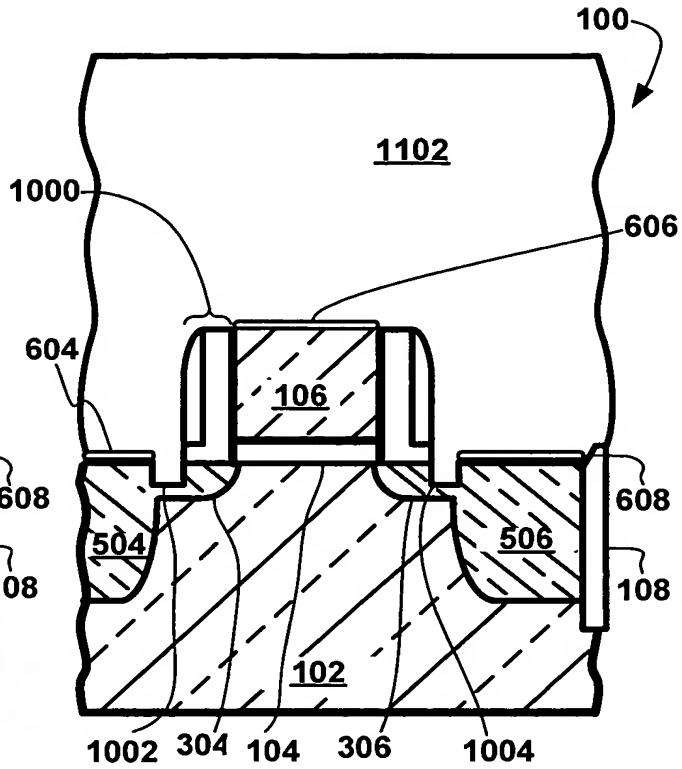

FIG. 11

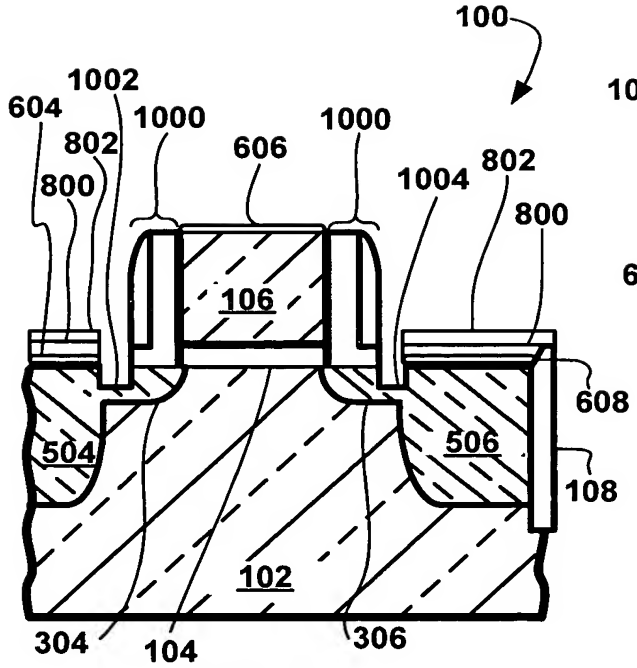

FIG. 10

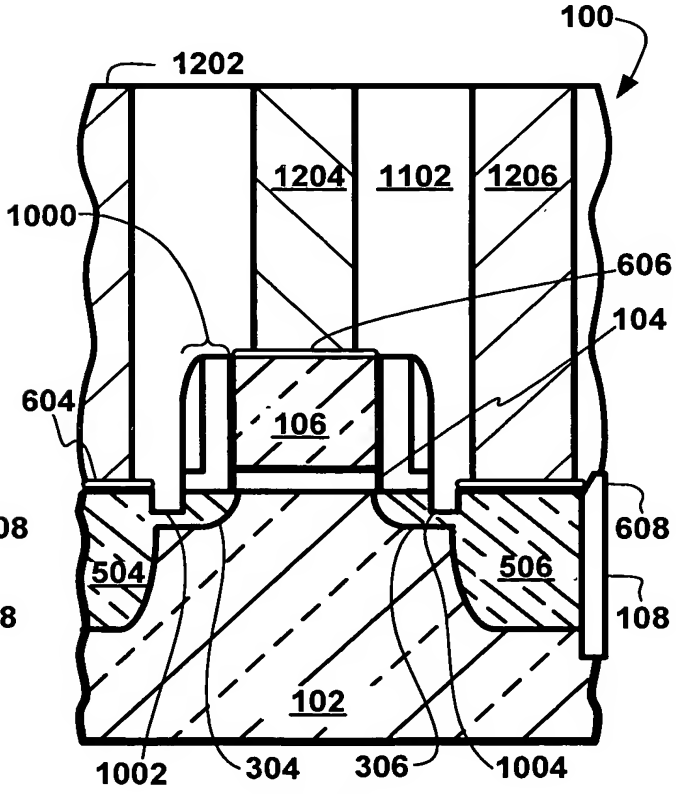

FIG. 12

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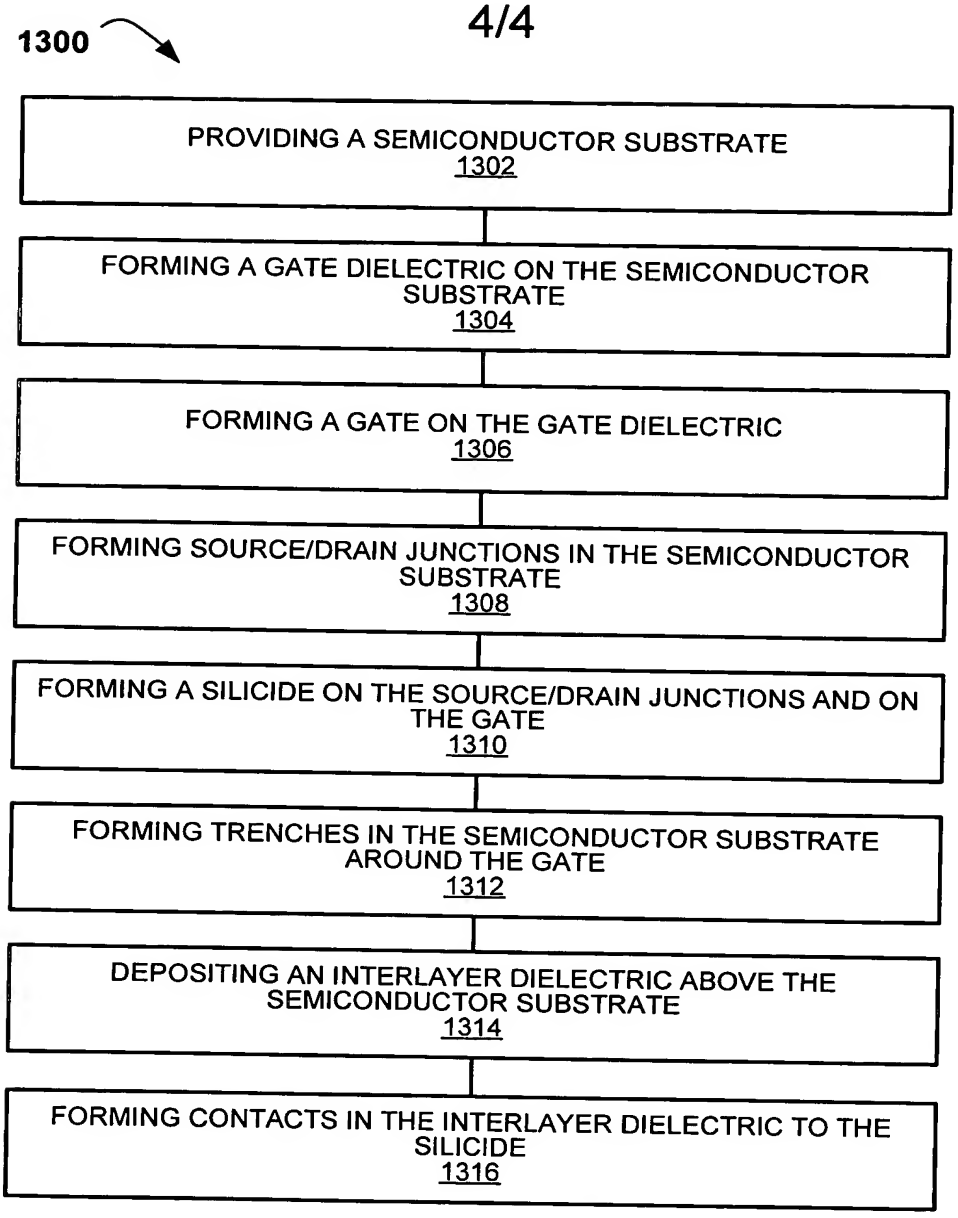

FIG. 13